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# **ON Semiconductor**®

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## FDB024N06 N-Channel PowerTrench<sup>®</sup> MOSFET 60 V, 265 A, 2.4 m $\Omega$

## Features

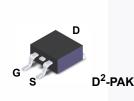
- $R_{DS(on)}$  = 1.8 m $\Omega$  (Typ.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low  $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

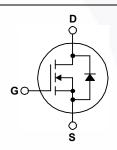
## Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench<sup>®</sup> process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

## Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Renewable System





## MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter	FDB024N06	Unit
V <sub>DSS</sub>	Drain to Source Voltage		60	V
V <sub>GSS</sub>	Gate to Source Voltage		±20	V
I <sub>D</sub>		- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C, Silicon Limited)	265	A
	Drain Current	- Continuous (T <sub>C</sub> = 100 <sup>o</sup> C, Silicon Limited)	190	
		- Continuous (T <sub>C</sub> = 25 <sup>o</sup> C, Package Limited)	120	
I <sub>DM</sub>	Drain Current	- Pulsed (Note 1)	1060	А
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		2531	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		6.0	V/ns
P <sub>D</sub>	Dower Dissinction	(T <sub>C</sub> = 25°C)	395	W
	Power Dissipation	- Derate Above 25°C	2.6	W/ºC
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
ΤL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Seconds	300	°C

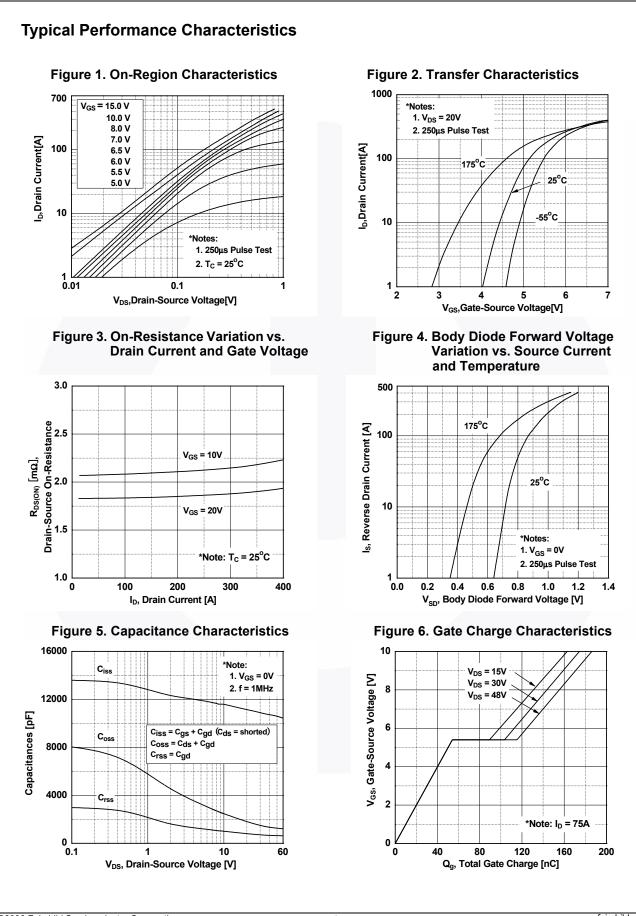
## Thermal Characteristics

Symbol	Parameter	FDB024N06	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.38	
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

FDB024N06
- N-Channel PowerTrench <sup>®</sup> MOSFET

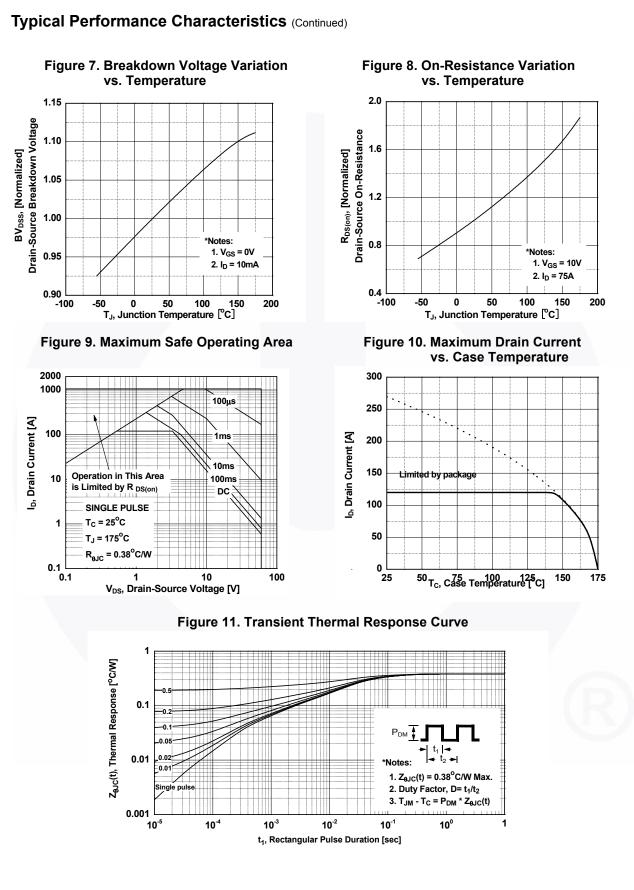
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5 FDB024N06 Characteristics T <sub>C</sub> = Parameter	D <sup>2</sup> -PA	K Tape and Re						
Parameter	= 25°C unles		eel	330 mm	Tape Width 24 mm		Quantity 800 units	
Parameter		ss otherwise noted.						
		Test Co	ndition	6	Min.	Тур.	Max.	Unit
ristics								
rain to Source Breakdown V	oltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub>	= 0 V		60	-	-	V
Breakdown Voltage Temperature						0.04		V/ºC
DSS Breakdown Voltage Temperature Coefficient						0.04	-	V/-C
Zero Gate Voltage Drain Current Gate to Body Leakage Current		$V_{DS} = 60 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 150^{\circ}\text{C}$			-	-		μA
		$v_{GS} = \pm 20 v, v_{DS}$	s = 0 v		-	-	±100	nA
ristics								
Bate Threshold Voltage					2.5	3.5	4.5	V
static Drain to Source On Res	sistance				-	1.8	2.4	mΩ
orward Transconductance		V <sub>DS</sub> = 10 V, I <sub>D</sub> = 75 A			-	200	-	S
aracteristics								
				-	11190	14885	pF	
output Capacitance			= 0 V,	-	-	1610	2140	pF
everse Transfer Capacitance	Э	f = 1 MHz		-	-	750	1125	pF
otal Gate Charge at 10V		V <sub>DS</sub> = 48 V, I <sub>D</sub> =	75 A,		-	174	226	nC
Sate to Source Gate Charge		V <sub>GS</sub> = 10 V		-	-	54	-	nC
Gate to Drain "Miller" Charge		(Note 4)		-	50	-	nC	
naracteristics								
	-			-	134	278	ns	
urn-On Rise Time				-	-	324	658	ns
urn-Off Delay Time		V <sub>GS</sub> = 10 V, R <sub>G</sub> =	25 Ω		-	348	706	ns
urn-Off Fall Time				(Note 4)	-	250	510	ns
Diode Characteristic	·e							
	-	do Forward Current					265	А
			•		-	-		A
		-	75 A		-	-		V
	a ronago				-		-	ns
		$dI_{F}/dt = 100 A/\mu s$			-	152	-	nC
	ero Gate Voltage Drain Currer ristics Gate Threshold Voltage tatic Drain to Source On Resonand Comparison orward Transconductance aracteristics aput Capacitance everse Transfer Capacitance total Gate Charge at 10V Gate to Source Gate Charge tate to Drain "Miller" Charge maracteristics urn-On Delay Time urn-Off Delay Time urn-Off Fall Time Diode Characteristic aximum Continuous Drain to aximum Pulsed Drain to Sou	coefficient   ero Gate Voltage Drain Current   cate to Body Leakage Current   ristics   cate Threshold Voltage   tatic Drain to Source On Resistance   orward Transconductance   aracteristics   mut Capacitance   everse Transfer Capacitance   otal Gate Charge at 10V   cate to Drain "Miller" Charge   aracteristics   urn-On Delay Time   urn-On Rise Time   urn-Off Delay Time   urn-Off Fall Time   e Diode Characteristics   aximum Continuous Drain to Source Diode F   rain to Source Diode Forward Voltage   everse Recovery Time	coefficient $I_D = 250 \ \mu A, Referenceero Gate Voltage Drain CurrentV_{DS} = 60 \ V, V_{GS} = V_{DS} = 60 \ V, V_{GS} = V_{DS} = 60 \ V, V_{GS} = 10 \ V, V_{DS} = 60 \ V, V_{GS} = 10 \ V, V_{DS} = 60 \ V, V_{GS} = 10 \ V, V_{DS} = 10 \ V, I_D = 10 \ V_{DS} = 10 \ V, I_S = 10 \ V_{DS} = 10 \ V_{DS}$	coefficient $I_D = 250 \ \mu$ A, Referencedero Gate Voltage Drain Current $V_{DS} = 60 \ V, V_{GS} = 0 \ V$ date to Body Leakage Current $V_{GS} = 60 \ V, V_{GS} = 0 \ V$ ristics $V_{GS} = 60 \ V, V_{GS} = 0 \ V$ date to Body Leakage Current $V_{GS} = 420 \ V, V_{DS} = 0 \ V$ ristics $V_{GS} = 10 \ V, I_D = 250 \ \mu$ Adate Threshold Voltage $V_{GS} = 10 \ V, I_D = 75 \ A$ orward Transconductance $V_{DS} = 10 \ V, I_D = 75 \ A$ aracteristics $V_{DS} = 10 \ V, I_D = 75 \ A$ aracteristics $V_{DS} = 25 \ V, V_{GS} = 0 \ V, f = 1 \ MHz$ bala Gate Charge at 10V $V_{DS} = 48 \ V, I_D = 75 \ A, V_{GS} = 10 \ V$ bala Gate Charge at 10V $V_{DS} = 48 \ V, I_D = 75 \ A, V_{GS} = 10 \ V$ bala Gate Charge at 10V $V_{DS} = 30 \ V, I_D = 75 \ A, V_{GS} = 10 \ V, R_G = 25 \ \Omega$ aracteristics $V_{DD} = 30 \ V, I_D = 75 \ A, V_{GS} = 10 \ V, R_G = 25 \ \Omega$ urn-Off Delay Time $V_{DS} = 10 \ V, R_G = 25 \ \Omega$ urn-Off Fall Time $V_{CS} = 10 \ V, R_G = 25 \ \Omega$ aximum Continuous Drain to Source Diode Forward Currentaximum Pulsed Drain to Source Diode Forward Currentrain to Source Diode Forward Voltage $V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, V_{GS} = 0 \ V, I_{SD} = 75 \ A, $	Image: Section of the section of t	looefficientID2.50 µA, Reterenced to $25^{\circ}$ C-ero Gate Voltage Drain Current $V_{DS} = 60 V, V_{GS} = 0 V$ -vate to Body Leakage Current $V_{GS} = 60 V, V_{GS} = 0 V, V_{CS} = 150^{\circ}$ C-ristics $V_{GS} = 220 V, V_{DS} = 0 V$ -risticssate Threshold Voltage $V_{GS} = V_{DS}, I_D = 250 \mu$ A2.5tatic Drain to Source On Resistance $V_{GS} = 10 V, I_D = 75 A$ -orward Transconductance $V_{DS} = 10 V, I_D = 75 A$ -aracteristicsaput Capacitance $V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz$ -everse Transfer Capacitanceotal Gate Charge at 10V $V_{DS} = 48 V, I_D = 75 A, f = 10 V, GS = $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

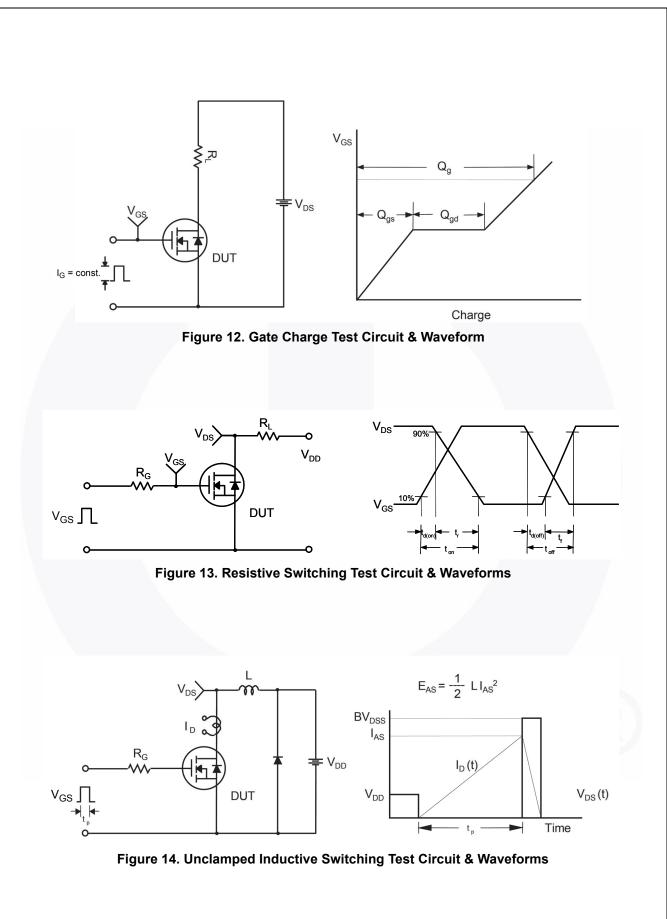


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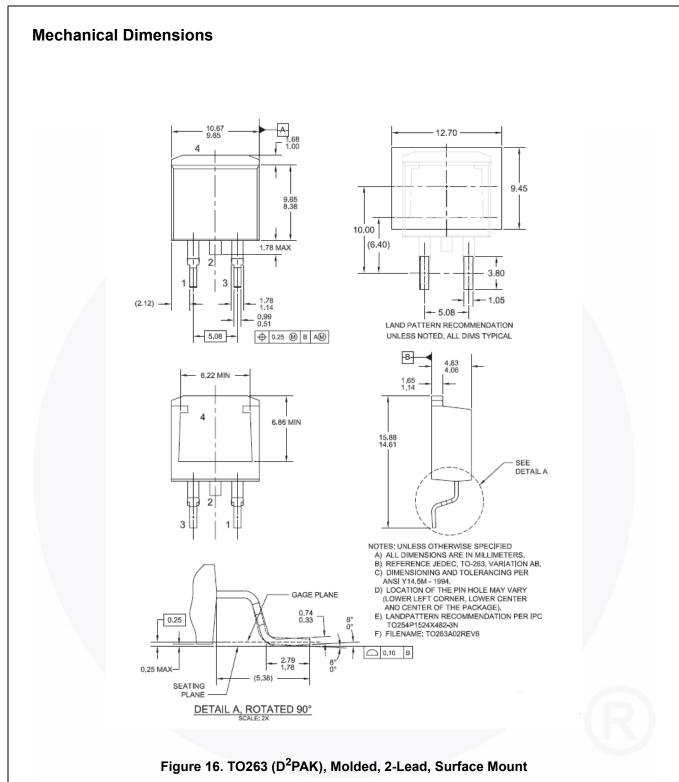
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4



DUT +  $V_{DS}$ a ۱<sub>SD</sub> م L Driver R<sub>G</sub>, Same Type as DUT L F ∨<sub>DD</sub>  $\prod V_{GS}$ • dv/dt controlled by  $R_{G}$ • I<sub>SD</sub> controlled by pulse period Î Gate Pulse Width  $\mathbf{V}_{\mathbf{GS}}$ D = Gate Pulse Period 10V (Driver) I<sub>FM</sub>, Body Diode Forward Current I <sub>SD</sub> di/dt (DUT)  $I_{RM}$ Body Diode Reverse Current  $V_{DS}$ (DUT) Body Diode Recovery dv/dt  $V_{SD}$ V<sub>DD</sub> Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



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**Телефон:** 8 (812) 309 58 32 (многоканальный) **Факс:** 8 (812) 320-02-42 **Электронная почта:** <u>org@eplast1.ru</u> **Адрес:** 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.